

ABSTRACT OF THE DISCLOSURE

A method of storing data in a ferroelectric memory device is capable of dealing with a program request during a read cycle or a change in program data during a program cycle. In this data storage method, the program cycle or the read cycle is performed for selected memory cells selected from among a plurality of memory cells, and each of the program cycle or the read cycle includes a period for writing data "0" and a period for writing data "1" into the selected memory cells. When a program request occurs in the period for writing the data "0" (read period) in the read cycle, the data "1" is written into the selected memory cells according to program data designated by the program request.